JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOD-323 Plastic-Encapsulate Diode

B5819WS SCHOTTKY BARRIER DIODE

FEATURES

Power dissipation

$P_{D:}$ 200 mW (Tamb=25℃)

Collector current

I_F: 1 A

Collector-base voltage

V_R: 40 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

MARKING: SL

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	I_R= 1mA	40		V
Reverse voltage leakage current	I_R	V_R=40V V_R=4V V_R=6V		1 0.05 0.075	mA
Forward voltage	V_F	I_F=0.1A I_F=1A I_F=3A		0.45 0.6 0.9	V
Diode capacitance	C_D	V_R=4V, f=1MHz		120	pF

Typical Characteristics

B5819WS

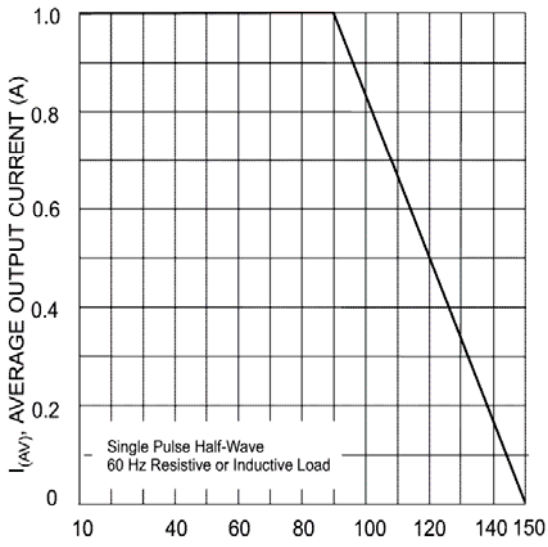
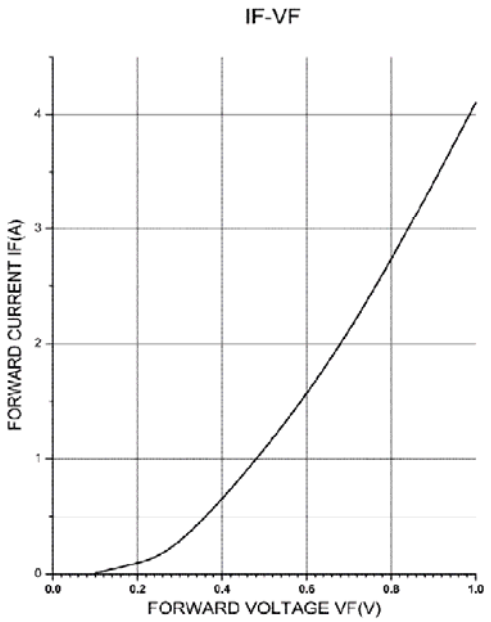


Fig. 1 Forward Current Derating Curve



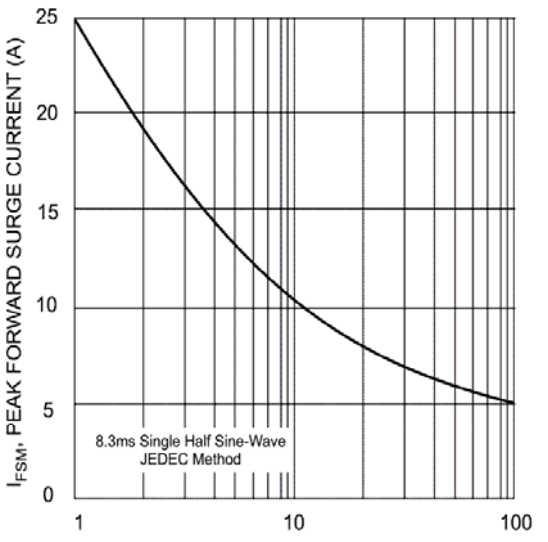


Fig. 3 Maximum Non-Repetitive Peak Fwd Surge Current

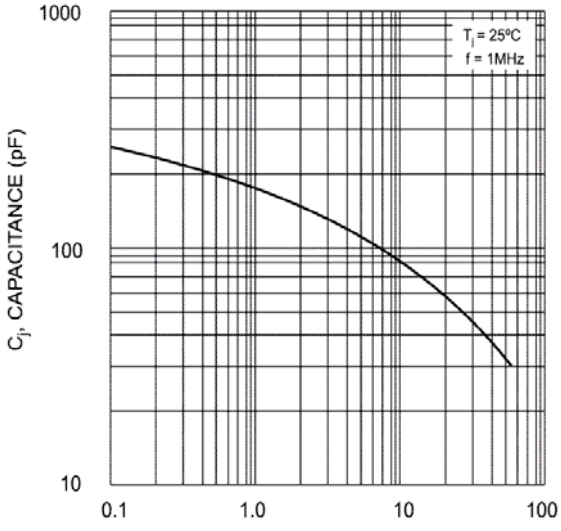


Fig. 4 Typical Junction Capacitance